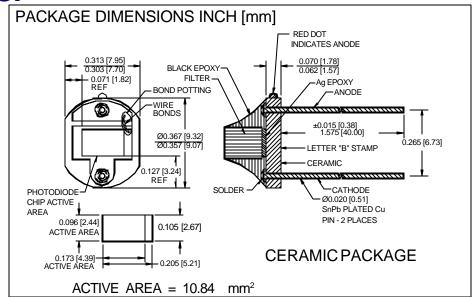
PHOTONIC DETECTORS INC.

Silicon Photodiode, U.V. Enhanced Photovoltaic (center wavelength 320 nm) Type PDU-V402B





FEATURES

- Built in filter
- U.V. enhanced
- I.R. blocking

DESCRIPTION

The **PDU-V402B** is a silicon, PIN planar diffused, U.V. enhanced photodiode. Ideal for low noise photovoltaic applications. The filter is a U.V. type B with a center wavelength of 320 nm, with 10⁻³ I.R. blocking. Packaged in a two leaded ceramic base.

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

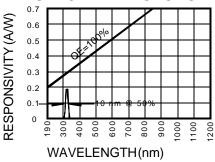
SYMBOL	PARAMETER	MIN	MAX	UNITS
VBR	Reverse Voltage		15	V
T _{STG}	Storage Temperature	-55	+100	⊙C
То	Operating Temperature Range	-40	+85	∘C
Ts	Soldering Temperature*		+260	⊙C
I _L	Light Current		0.5	mA

^{*1/16} inch from case for 3 secs max

APPLICATIONS

- U.V. detection
- U.V. A sensor
- U.V. radiometer

SPECTRALRESPONSE



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Isc	Short Circuit Current	H = 100 fc, 2850 K	20	30		μΑ
ΙD	Dark Current	$H = 0, V_R = 10 \text{ mV}$		5	10	nA
RsH	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$	100	200		MΩ
TC Rsh	RSH Temp. Coefficient	$H = 0, V_R = 10 \text{ mV}$		-8		%/℃
Cı	Junction Capacitance	$H = 0, V_R = 0 V^{**}$		1250		рF
λrange	Spectral Application Range	Spot Scan	300	320	340	nm
R	Responsivity	$V_{R} = 0 \text{ V}, \ \lambda = 320 \text{ nm}$.08		A/W
VBR	Breakdown Voltage	I = 10 μA	15	30		V
NEP	Noise Equivalent Power	VR = 2 V @ Peak		1x10 ⁻¹⁴		W/ √ Hz
tr	Response Time	$RL = 1 K\Omega V_R = 0 V$		1000		nS